

22. The method of claim **21**, wherein the metal material includes a metal selected from the group consisting of chromium, tungsten, and copper, cobalt, indium, and combinations thereof.

23. The method of claim **21**, further comprising forming a metal chalcogenide layer between the chalcogenide glass layer and the ion source structure.

24. The method of claim **21**, wherein forming the ion source structure comprises:

- forming a first adhesion layer;
- forming a metal layer; and
- forming a second adhesion layer.

25. A variable resistance memory device comprising:

- a first electrode and a second electrode;
- a chalcogenide glass layer between the first electrode and the second electrode, the chalcogenide glass layer including a chalcogenide glass material co-deposited with a metal material;
- a metal ion source structure between the chalcogenide glass layer and the second electrode; and
- a buffer layer between the first electrode and the chalcogenide glass layer, wherein the buffer layer continuously covers the first electrode.

26. The device of claim **25**, wherein the buffer layer includes the chalcogenide glass material and excludes the metal material.

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